

# How Automotive Mission Profiles Relate to Semiconductor Reliability Testing

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September 30th, 2020



# Agenda

What Is a Mission Profile?

Stress to the Silicon

IC Qualification

Assessment of Existing and Qualified Components

Fail Mech, Models, Acceleration Factor

Equivalent Qualification Stress

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Open Q&A

# What is a Mission Profile?

A Mission Profile is a mirror image of the expected life time of an application and the associated stress, which all used device will be submitted to.

It is needed to estimate if all used device will be reliable enough to maintain the specified product performance at least over the projected life time.

Most common is the Mission Profile that details the life time and associated use temperatures in form of a table. Other MPs specify also mechanical stress or stress that comes along with humidity.

Operating Lifetime 15 years			
Profile 1			
Active		Passive	
Tj in °C	hours	Tj in °C	hours
-40	45	-40	346
20	45	15	21168
40	855	25	42336
50	3150	35	21168
60	4950	40	1382
70	9000		86400
80	11250		
90	6750		
100	4950		
110	2700		
120	1170		
125	135		
	45000		
Total hours	131400		

# Stress to the Silicon

What stress is it that the used devices will see during their life time?


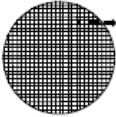
Thermo-Mechanical :            the applications will be switched on/off and are used in winter and summer time etc.

Voltage- and Temperature:    Voltage (current) as well as temperature will cause aging effects to the silicon-junction

The stresses will impact the material properties over life time and will (slowly) degrade the device performance. This can compromise the electrical performance as well as the mechanical performance.

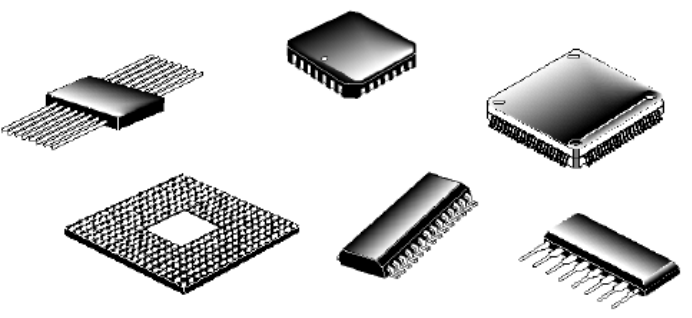
There are numerous standards that define certain qualification tests, which are designed to provoke certain reliability fail mechanisms. In semiconductors the most used standards are JEDEC and AEC.

# IC Qualification



**AEC - Q100 - Rev-H**  
**September 11, 2014**

**FAILURE MECHANISM BASED  
STRESS TEST QUALIFICATION  
FOR  
INTEGRATED CIRCUITS**

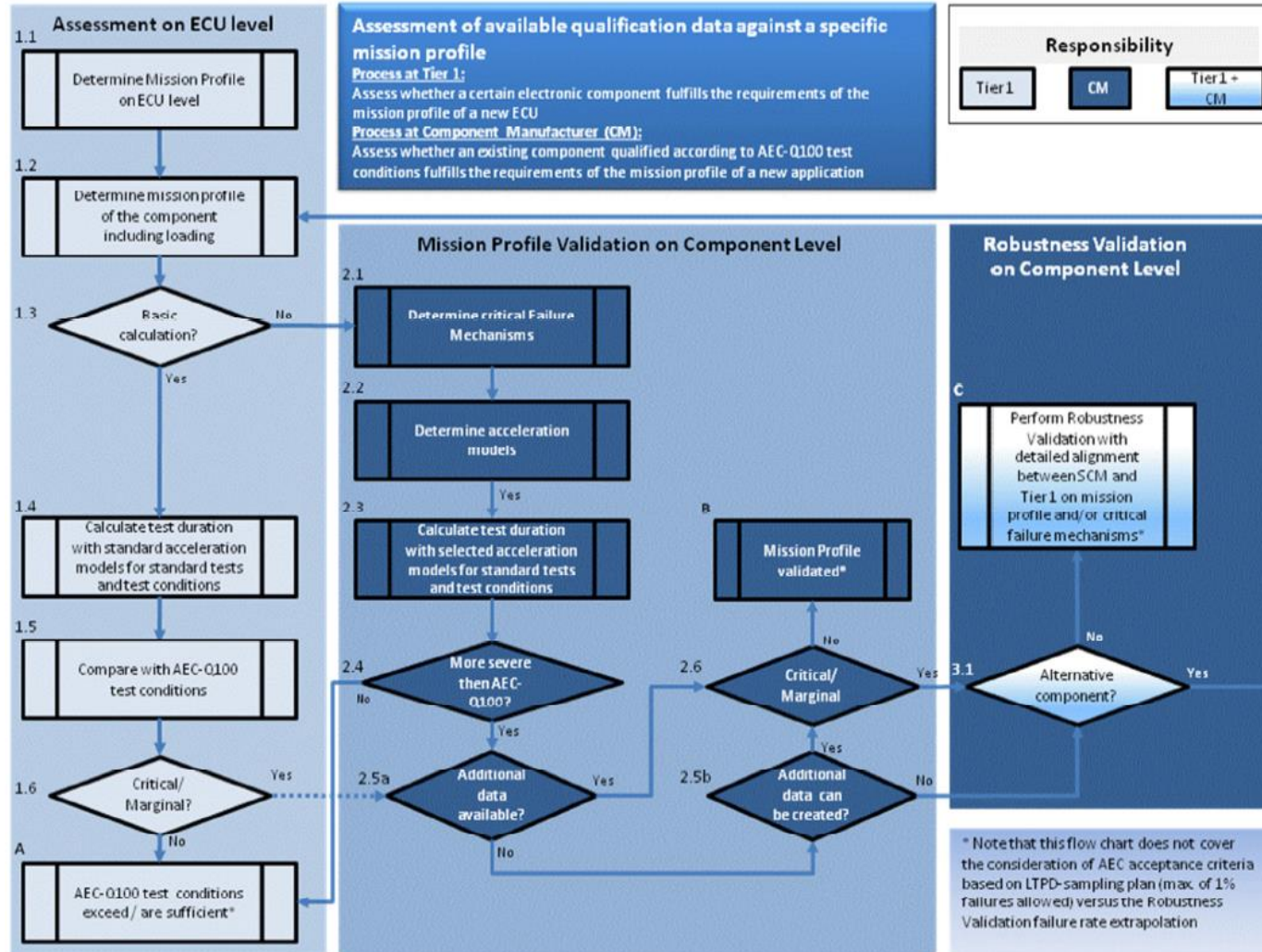


**Automotive Electronics Council**  
Component Technical Committee

Appendix Template 4A: AEC-Q100 Qualification Test Plan

Q100H QUALIFICATION TEST PLAN							
USER COMPANY:		DATE:					
USER PIN:		TRACKING NUMBER:					
USER SPEC #:		USER COMPONENT ENGINEER:					
SUPPLIER COMPANY:		SUPPLIER MANUFACTURING SITES:					
SUPPLIER PIN:		PPAP SUBMISSION DATE:					
SUPPLIER FAMILY TYPE:		REASON FOR QUALIFICATION:					
STRESS TEST	ABV	TEST#	TEST METHOD	Test Conditions/S.S. per Lot/# Lots (identify temp, RH, & bias)	REQUIREMENTS S.S.	# LOTS	RESULTS Failures/S.S./# lots
Preconditioning	PC	A1	JEDEC J-STD-020	Peak Reflow Temp. - Preconditioning used -	Min. MSL - 3	MSL -	
Temperature Humidity Bias or HAST	THB / HAST	A2	JESD22-A101/A110		77	3	
Autoclave or Unbiased HAST	AC / UHST	A3	JESD22-A102/A118		77	3	
Temperature Cycle	TC	A4	JESD22-A104		77	3	
Power Temperature Cycling	PTC	A5	JESD22-A105		45	1	
High Temperature Storage Life	HTSL	A6	JESD22-A103		45	1	
High Temperature Operating Life	HTOL	B1	JESD22-A108		77	3	
Early Life Failure Rate	ELFR	B2	AEC Q100-006		800	3	
NVM Endurance, Data Retention, & Operational Life	EDR	B3	AEC Q100-005		77	3	
Wire Bond Shear	WBS	C1	AEC Q100-001		5	1	
Wire Bond Pull Strength	WBP	C2	MIL-STD-883 - 2011		5	1	
Temperature Cycle	TC	A4	JESD22-A104				
Power Temperature Cycling	PTC	A5	JESD22-A105				
High Temperature Storage Life	HTSL	A6	JESD22-A103				
High Temperature Operating Life	HTOL	B1	JESD22-A108				
Early Life Failure Rate	ELFR	B2	AEC Q100-006				
NVM Endurance, Data Retention, & Operational Life	EDR	B3	AEC Q100-005				
Wire Bond Shear	WBS	C1	AEC Q100-001				
Electrical Distributions	ED	E5	AEC Q100-009		30	3	
Fault Grading	FG	E6	AEC-Q100-007				
Characterization	CHAR	E7	AEC Q003				
Electromagnetic Compatibility	EMC	E9	SAE J1752/3		1	1	
Short Circuit Characterization	SC	E10	AEC Q100-012		10	3	
Soft Error Rate	SER	E11	JESD69-1, -2, -3		3	1	
Lead Free	LF	E12	Q005				
Process Average Test	PAT	F1	AEC Q001				
Statistical Bin/Yield Analysis	SBA	F2	AEC Q002				
Hermetic Package Tests	MECH	G1-4	Series		15	1	
Package Drop	DROP	G5			5	1	
Lid Torque	LT	G6	MIL-STD-883 - 2024		5	1	
Die Shear Strength	DS	G7	MIL-STD-883 - 2019		5	1	
Internal Water Vapor	IWV	G8	MIL-STD-883 - 1018		5	1	
Supplier:				Approved by: (User Engineer)			

# Assessment of Existing and Qualified Components



AECQ100 defines that the Tier1 shall perform the assessment of the reliability capability on ECU level.

AECQ100, Rev H; Figure A7.2: Flow Chart 2



# Fail Mech, Models, Acceleration Factor

<u>Loading</u>	<u>Mission Profile Input</u>	<u>Stress Test</u>	<u>Stress Conditions</u>	<u>Acceleration Model</u> (all temperatures in K, not in °C)	<u>Model Parameters</u>	<u>Calculated Test Duration</u>	<u>Q100 Test Duration</u>
<u>Operation</u>	<u><math>t_u = 12,000</math> hr</u> <u>(average operating use time over 15 yr)</u>  <u><math>T_u = 87^\circ\text{C}</math></u> <u>(average junction temperature in use environment)</u>	<u>High Temperature Operating Life (HTOL)</u>	<u><math>T_t = 125^\circ\text{C}</math></u> <u>(junction temperature in test environment)</u>	<u>Arrhenius</u>  $A_f = \exp\left[\frac{E_a}{k_B} \cdot \left(\frac{1}{T_u} - \frac{1}{T_t}\right)\right]$  <u>Also applicable for High Temperature Storage Life (HTSL) and NVM Endurance, Data Retention Bake, &amp; Operational Life (EDR)</u>	<u><math>E_a = 0.7</math> eV</u> <u>(activation energy; 0.7 eV is a typical value, actual values depend on failure mechanism and range from -0.2 to 1.4 eV)</u>  <u><math>k_B = 8.61733 \times 10^{-5}</math> eV/K</u> <u>(Boltzmann's Constant)</u>	<u><math>t_t = 1393</math> hr</u> <u>(test time)</u>  $t_t = \frac{t_u}{A_f}$	<u>1000 hr</u>
<u>Thermo-mechanical</u>	<u><math>n_u = 54,750</math> cls</u> <u>(number of engine on/off cycles over 15 yr of use)</u>  <u><math>\Delta T_u = 76^\circ\text{C}</math></u> <u>(average thermal cycle temperature change in use environment)</u>	<u>Temperature Cycling (TC)</u>	<u><math>\Delta T_t = 205^\circ\text{C}</math></u> <u>(thermal cycle temperature change in test environment: -55°C to +150°C)</u>	<u>Coffin Manson</u>  $A_f = \left(\frac{\Delta T_t}{\Delta T_u}\right)^m$  <u>Also applicable for Power Temperature Cycle (PTC)</u>	<u><math>m = 4</math></u> <u>(Coffin Manson exponent; 4 is to be used for cracks in hard metal alloys, actual values depend on failure mechanisms and range from 1 for ductile to 9 for brittle materials)</u>	<u><math>n_t = 1034</math> cls</u> <u>(number of cycles in test)</u>  $n_t = \frac{n_u}{A_f}$	<u>1000 cls</u>

AECQ100, Rev G; Table A7.1: Basic Calculations for AEC-Q100 Stress Test Conditions and Durations

AECQ100 also to a loading of “Humidity”, but this is typically not requested to us

# Equivalent Qualification Stress

In order to check if a certain device is suitable for a given MP, the stress of the MP must be translated into equivalent qualification stress.

Mission Profile Stress - > Equivalent Qual Stress > or < Qualification Stress

The associated acceleration models “Arrhenius” and/or “Coffin-Manson” provide the equations that needs be used.



# Equivalent Qualification Stress - Example

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Profile 1			
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100	4950		
110	2700		
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125	135		
	45000		
Total hours	131400		

$$Af = \exp\left(\frac{Ea}{kb}\right) * \left(\frac{1}{273 - 40} - \frac{1}{273 + 125}\right)$$

$$Af = 4184927.76$$

$$tt = \frac{tu}{Af}$$

$$tt = \frac{45h}{4184927.76}$$

$$tt = 0.0000107h$$

Arrhenius

$$A_f = \exp\left[\frac{E_a}{k_B} \cdot \left(\frac{1}{T_u} - \frac{1}{T_l}\right)\right]$$

This calculation needs to be done for every profile increment and the total equivalent test time is the sum of all tts.

For this Profile 1 the total equivalent test time is ~5888h.

The typical AECQ100 HTOL testing is only 1000h.

-> the MP stress exceeds the qual stress by factor ~6.

-> there is a certain risk that there will be device failures towards the end of the projected application life time.

# Equivalent Qualification Stress – Example cont'd

How to address this?

- Either the actual  $T_j$  can be reduced in the application by implementing cooling/heat sink
- Extend the qualification by prolonging the test time and/or the increase the  $T_j$

Using a qualification  $T_j$  of 150C the total equivalent test time would be ~1767h.

With a test time of 1000h there would still be a little risk for device failures towards the end of the projected application life time.

If we additionally increased the test duration, say to 2000h, the qual stress would be significantly higher than the expected life time stress. This would provide a very high level of confidence that the device would not compromise operating performance or cause failures towards the end of the projected application life time.

**Thanks !**